

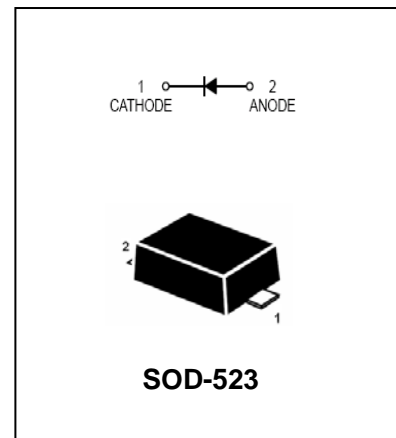
Schottky Barrier Diode

FEATURES

- Low $I_R=0.1\mu A$.
- High reliability.
- Small surface mounting.

APPLICATIONS

- Low current rectification.



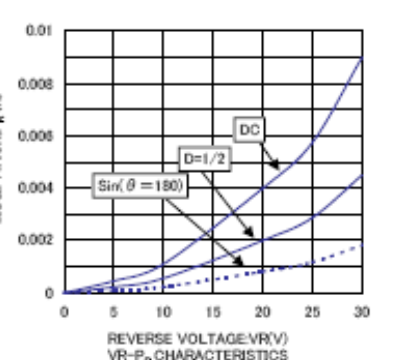
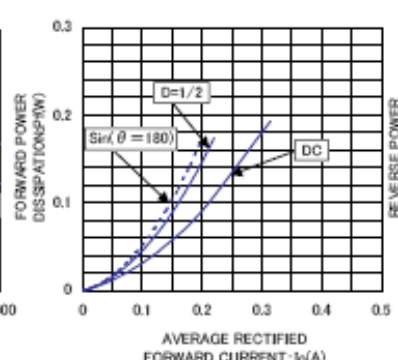
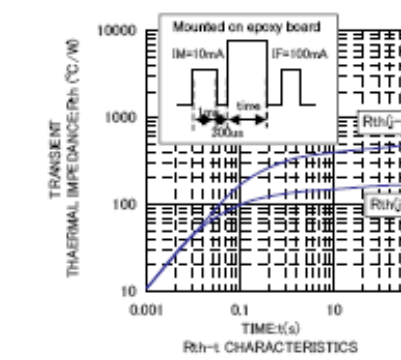
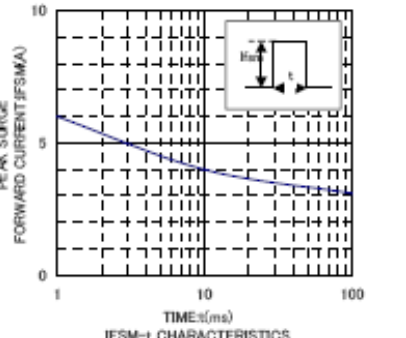
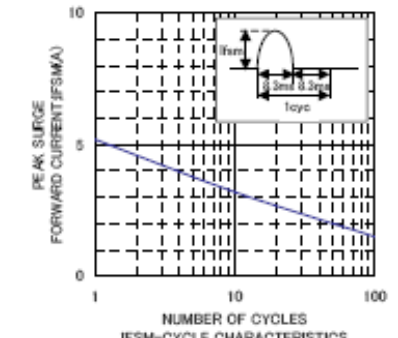
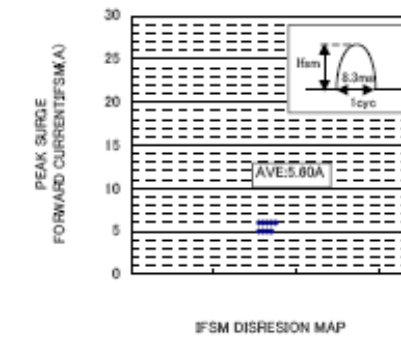
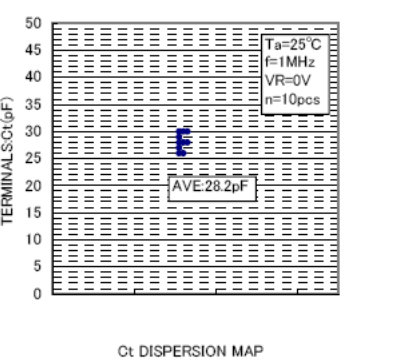
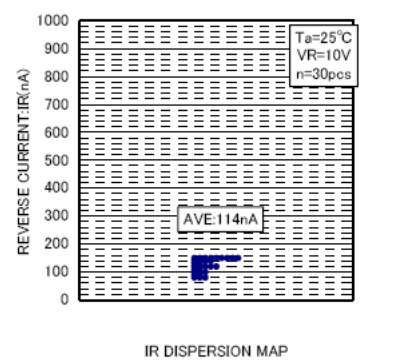
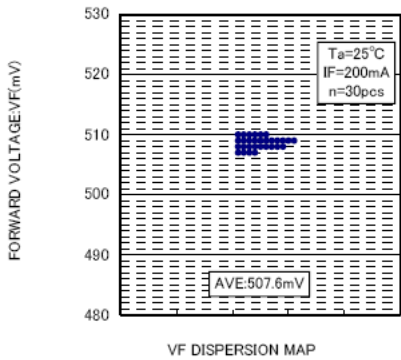
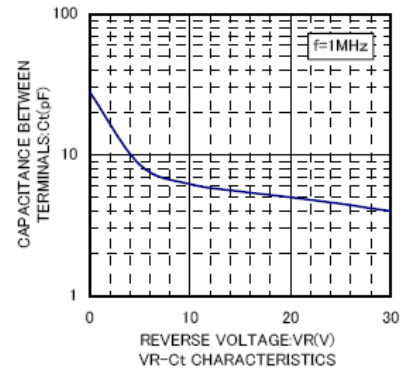
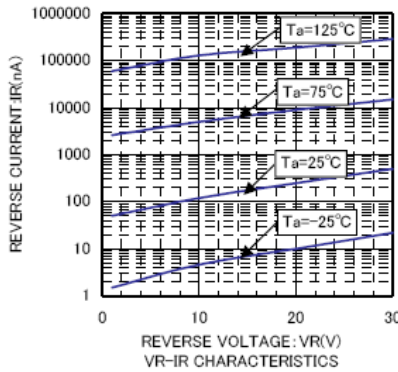
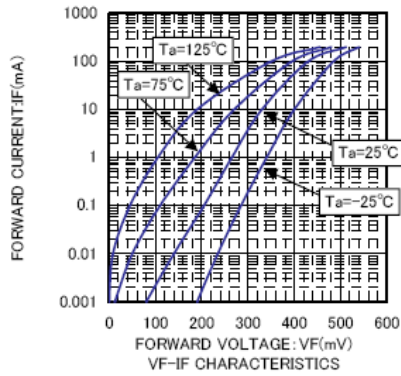
MAXIMUM RATING @ $T_a=25^\circ C$ unless otherwise specified

Parameter	Symbol	Limits	Unit
DC reverse voltage	V_R	30	V
Mean rectifying current	I_o	200	mA
Peak forward surge current	I_{FSM}	1	A
Total device dissipation	P_T	200	mW
Junction and storage temperature	T_j, T_{stg}	-40 to +125	$^\circ C$

ELECTRICAL CHARACTERISTICS @ $T_a=25^\circ C$ unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_F			0.6	V	$I_F=200mA$
Reverse current	I_R			1	μA	$V_R=10V$

TYPICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified



PACKAGE OUTLINE

Plastic surface mounted package

SOD-523

